

	Hits	Search Text	DBs
1	10	((resist or photoresist or photosensitive or (radiation near5 sensitive)) same pattern\$4 same (expos\$4 or irradiat\$4 or illuminat\$4) same (etch\$4 or (dry near5 etch\$4) or RIE) same (sidewall or side\$8 or top\$3portion or top\$4area)) and develop\$4 and ((resist or photoresist or photosensitive) same pattern\$4 same (etch\$4 or RIE) same (gas\$4 or (inert\$4 near5 gas\$3) or plasma or ion\$3beam or ion\$4) same ((sulfur near7 oxide) or (sul\$3ur near9 \$2oxide) or ("SO.sub.2")) same (He or Ne or Ar or Xe or Kr or "N.sub.2"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
2	21	((resist or photoresist or photosensitive or (radiation near5 sensitive)) same pattern\$4 same (etch\$4 or (dry near5 etch\$4) or RIE) same (sidewall or side\$8 or top\$3portion or top\$4area or (upper near6 (portion or area)))) and develop\$4 and ((resist or photoresist or photosensitive) same pattern\$4 same (etch\$4 or RIE) same (gas\$4 or (inert\$4 near5 gas\$3) or plasma or ion\$3beam or ion\$4) same ((sulfur near7 oxide) or (sul\$3ur near9 \$2oxide) or ("SO.sub.2")) same (He or Ne or Ar or Xe or Kr or "N.sub.2")) and (expos\$4 or irradiat\$4 or illuminat\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
3	8	((resist or photoresist or photosensitive or (radiation near5 sensitive)) same pattern\$4 same ((etch\$4 or (dry near5 etch\$4) or RIE) near9 (sidewall or side\$8 or top\$3portion or top\$4area or top\$4side or top\$6wall))) and ((resist or photoresist or photosensitive) same pattern\$4 same (etch\$4 or RIE) same (gas\$4 or (inert\$4 near5 gas\$3) or plasma or ion\$3beam or ion\$4) same ((sulfur near7 oxide) or (sul\$3ur near9 \$2oxide) or ("SO.sub.2"))) same (He or Ne or Ar or Xe or Kr or "N.sub.2")) and (expos\$4 or irradiat\$4 or illuminat\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
4	13	((resist or photoresist or photosensitive or (radiation near5 sensitive)) same pattern\$4 same (etch\$4 or (dry near5 etch\$4) or RIE) same (ARC or antireflect\$4 or BARC or TARC) same (film or coat\$4 or deposit\$4 or layer)) and ((resist or photoresist or photosensitive) same pattern\$4 same (etch\$4 or RIE) same (gas\$4 or (inert\$4 near5 gas\$3) or plasma or ion\$3beam or ion\$4) same ((sulfur near7 oxide) or (sul\$3ur near9 \$3oxide) or ("SO.sub.2")))) and (expos\$4 or irradiat\$4 or illuminat\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
5	264	((resist or photoresist or photosensitive or (radiation near5 sensitive)) same pattern\$4 same (etch\$4 or (dry near5 etch\$4) or RIE) same (ARC or antireflect\$4 or BARC or TARC) same (film or coat\$4 or deposit\$4 or layer) same organic) and ((resist or photoresist or photosensitive) same pattern\$4 same (etch\$4 or RIE) same (gas\$4 or (inert\$4 near5 gas\$3) or plasma or ion\$3beam or ion\$4) same (expos\$4 or irradiat\$4 or illuminat\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB